

DFM750AXM65-TS000

Fast Recovery Diode Module

DS6176-1 July 2015 (LN32793)

FEATURES

- Low Reverse Recovery Charge
- · High Switching Speed
- Low Forward Volt Drop
- Isolated AISiC Base With AIN Substrates
- Triple Diodes can be paralleled for 2250A Rating

APPLICATIONS

- Brake Chopper Diodes
- Boost and Buck Converters
- Free-wheel Circuits
- Motor Drives
- Resonant Converters
- Induction Heating
- Multi-level Switch Inverters

The DFM750AXM65-TS000 is a triple 6500V, fast recovery diode (FRD) module. Designed for low power loss, the module is suitable for a variety of high voltage applications in motor drives and power conversion.

Fast switching times and low reverse recovery losses allow high frequency operation, making the device suitable for the latest drive designs employing PWM and high frequency switching.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DFM750AXM65-TS000

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{RRM}		6500V
V_{F}	(typ)	3.6V
I _F	(max)	750A
I _{FM}	(max)	1500A

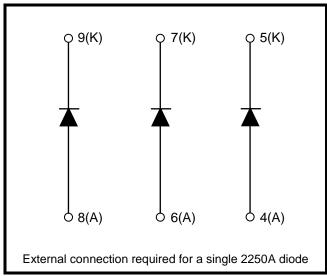


Fig. 1 Circuit configuration



Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
		T _j = 125°C	6500	V
V_{RRM}	Repetitive peak reverse voltage	T _j = 25°C	6500	V
		$T_j = -40$ °C	6000	V
I _F	Forward current (per arm)	DC, T _{case} = 60°C, T _j = 125°C	750	Α
I _{FM}	Max. forward current	$T_{case} = 110^{\circ}C, t_p = 1ms$	1500	Α
l ² t	I ² t value fuse current rating	$V_R = 0$, $t_p = 10$ ms, $T_j = 125$ °C	200	kA ² s
P _{max}	Max. power dissipation	T _{case} = 25°C, T _j = 125°C	5000	W
V _{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	10.2	kV
Q_{PD}	Partial discharge – per module	IEC1287, V ₁ = 6900V, V ₂ = 5100V, 50Hz RMS	10	рС

THERMAL AND MECHANICAL RATINGS

Internal insulation material:

Baseplate material:

Creepage distance:

Clearance:

CTI (Comparative Tracking Index):

AIN

AISiC

56mm

26mm

> 600

Symbol	Parameter	Test Conditions	Min	Тур.	Max	Units
R _{th(j-c)}	Thermal resistance (per arm)	Continuous dissipation – junction to case	-	-	20	°C/kW
R _{th(c-h)}	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	6	°C/kW
Tj	Junction temperature		-40	-	125	°C
T _{stg}	Storage temperature range		-40	-	125	°C
	Screw Torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M8	-	-	10	Nm

STATIC ELECTRICAL CHARACTERISTICS - PER ARM

 T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
I _{RM}	Peak reverse current	V _R = 6500V, T _j = 125°C			50	mA
V _F	Forward voltage	I _F = 750A		3.6		V
		I _F = 750A, T _j = 125°C		4.3		V
L _M	Inductance	-		40		nΗ

STATIC ELECTRICAL CHARACTERISTICS

 T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
L _M	Module inductance (externally connected in parallel)	-		13		nΗ
R _{INT}	Internal resistance (per arm)	-		370		μΩ

DYNAMIC ELECTRICAL CHARACTERISTICS - PER ARM

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Тур.	Max	Units
Q_{rr}	Reverse recovery charge	$I_F = 750A$ $V_R = 3600V$ $dI_F/dt = 2000A/\mu s$		1300		μC
I _{rr}	Peak reverse recovery current			830		Α
E _{rec}	Reverse recovery energy			3000		mJ

T_{case} = 125°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Тур.	Max	Units
Q_{rr}	Reverse recovery charge	I _F =750A		2100		μC
I _{rr}	Peak reverse recovery current	$V_R = 3600V$ $dI_F/dt = 2000A/\mu s$		950		Α
E _{rec}	Reverse recovery energy			4800		mJ

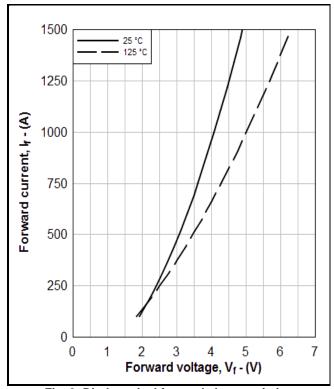


Fig. 3 Diode typical forward characteristics

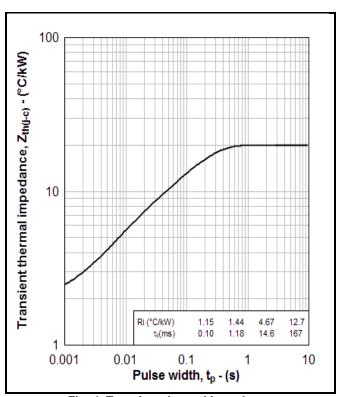


Fig. 4 Transient thermal impedance

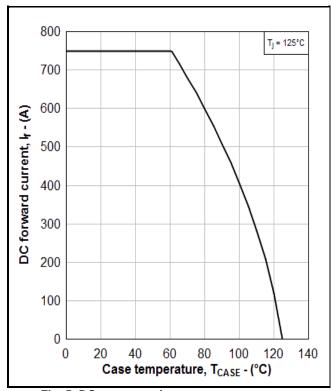


Fig. 5 DC current rating vs case temperature

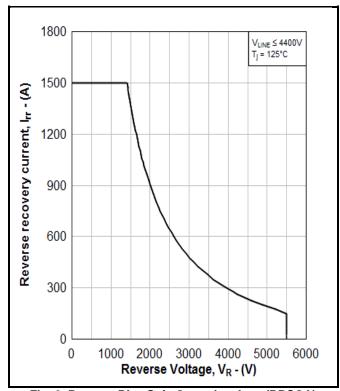


Fig. 6 Reverse Bias Safe Operating Area (RBSOA)

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services. All dimensions in mm, unless stated otherwise.

DO NOT SCALE.

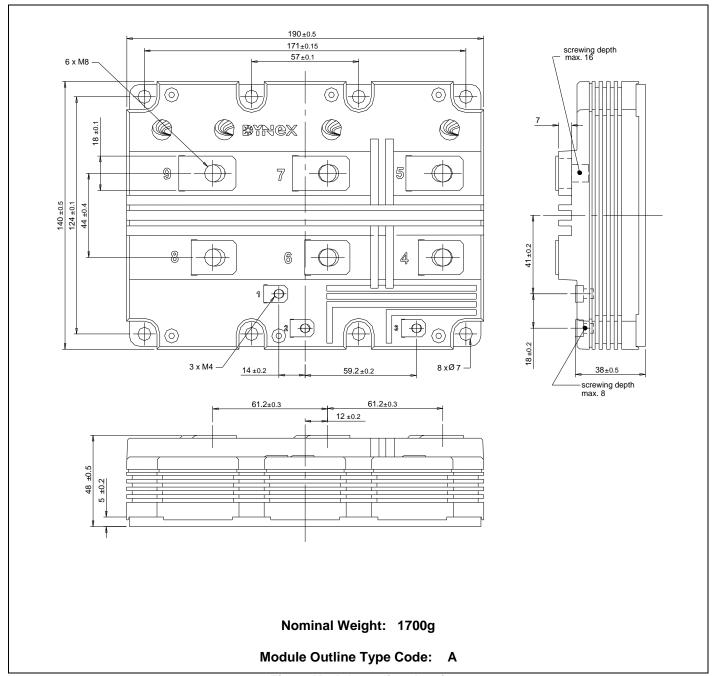


Fig. 7 Module outline drawing

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